

# BTA312X series B and C

12 A Three-quadrant triacs high commutation

Rev. 01 — 11 April 2007

Product data sheet

## 1. Product profile

### 1.1 General description

Passivated, new generation, high commutation triacs in a SOT186A full pack plastic package

### 1.2 Features

- Very high commutation performance maximized at each gate sensitivity
- High immunity to dV/dt
- High isolation voltage

### 1.3 Applications

- High power motor control - e.g. washing machines, vacuum cleaners
- Refrigeration and air conditioning compressors
- Non-linear rectifier-fed motor loads
- Electronic thermostats

### 1.4 Quick reference data

- $V_{DRM} \leq 600$  V (BTA312X-600B/C)
- $I_{GT} \leq 50$  mA (BTA312X-series B)
- $V_{DRM} \leq 800$  V (BTA312X-800B)
- $I_{GT} \leq 35$  mA (BTA312X-600C)
- $I_{TSM} \leq 95$  A ( $t = 20$  ms)
- $I_{T(RMS)} \leq 12$  A

## 2. Pinning information

Table 1. Pinning

Pin	Description	Simplified outline	Symbol
1	main terminal 1 (T1)	<p>SOT186A (TO-220F)</p>	<p>sym051</p>
2	main terminal 2 (T2)		
3	gate (G)		
mb	mounting base; isolated		

### 3. Ordering information

**Table 2.** Ordering information

Type number	Package		Version
	Name	Description	
BTA312X-600B	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220 'full pack'	SOT186A
BTA312X-600C			
BTA312X-800B			

### 4. Limiting values

**Table 3.** Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{\text{DRM}}$	repetitive peak off-state voltage	BTA312X-600B; BTA312X-600C	[1]	600	V
		BTA312X-800B	-	800	V
$I_{\text{T(RMS)}}$	RMS on-state current	full sine wave; $T_{\text{h}} \leq 61\text{ }^{\circ}\text{C}$ ; see Figure 4 and 5	-	12	A
$I_{\text{TSM}}$	non-repetitive peak on-state current	full sine wave; $T_{\text{j}} = 25\text{ }^{\circ}\text{C}$ prior to surge; see Figure 2 and 3			
		$t = 20\text{ ms}$	-	95	A
		$t = 16.7\text{ ms}$	-	105	A
$I^2t$	$I^2t$ for fusing	$t = 10\text{ ms}$	-	45	$\text{A}^2\text{s}$
$di_{\text{T}}/dt$	rate of rise of on-state current	$I_{\text{TM}} = 20\text{ A}$ ; $I_{\text{G}} = 0.2\text{ A}$ ; $di_{\text{G}}/dt = 0.2\text{ A}/\mu\text{s}$	-	100	$\text{A}/\mu\text{s}$
$I_{\text{GM}}$	peak gate current		-	2	A
$P_{\text{GM}}$	peak gate power		-	5	W
$P_{\text{G(AV)}}$	average gate power	over any 20 ms period	-	0.5	W
$T_{\text{stg}}$	storage temperature		-40	+150	$^{\circ}\text{C}$
$T_{\text{j}}$	junction temperature		-	125	$^{\circ}\text{C}$

- [1] Although not recommended, off-state voltages up to 800 V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 15 A/ $\mu\text{s}$ .

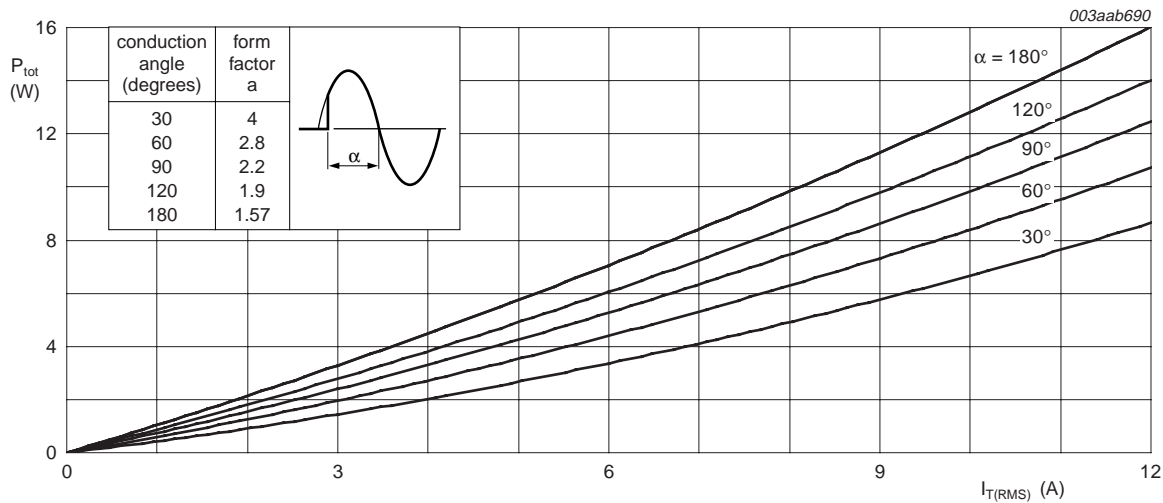


Fig 1. Total power dissipation as a function of RMS on-state current; maximum values

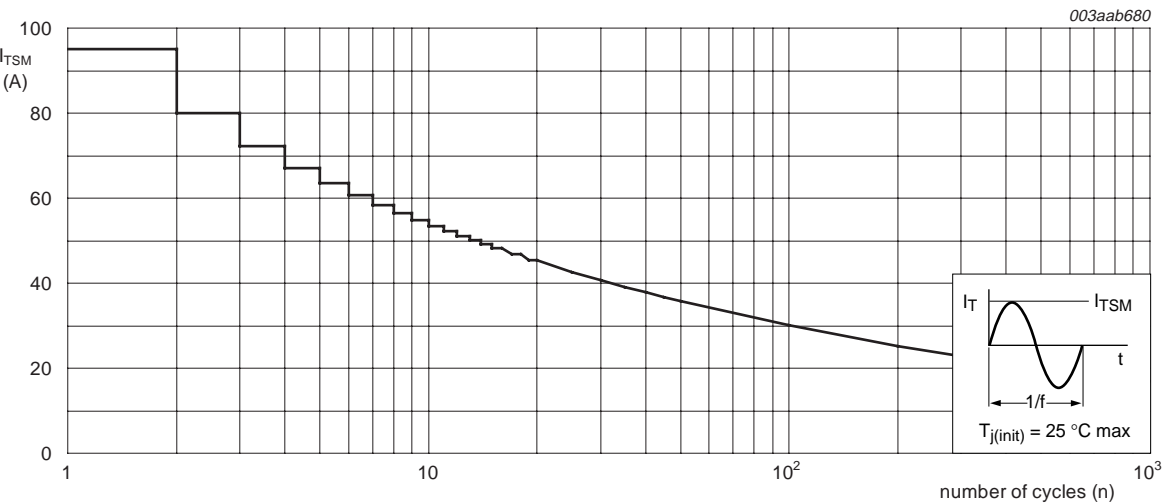
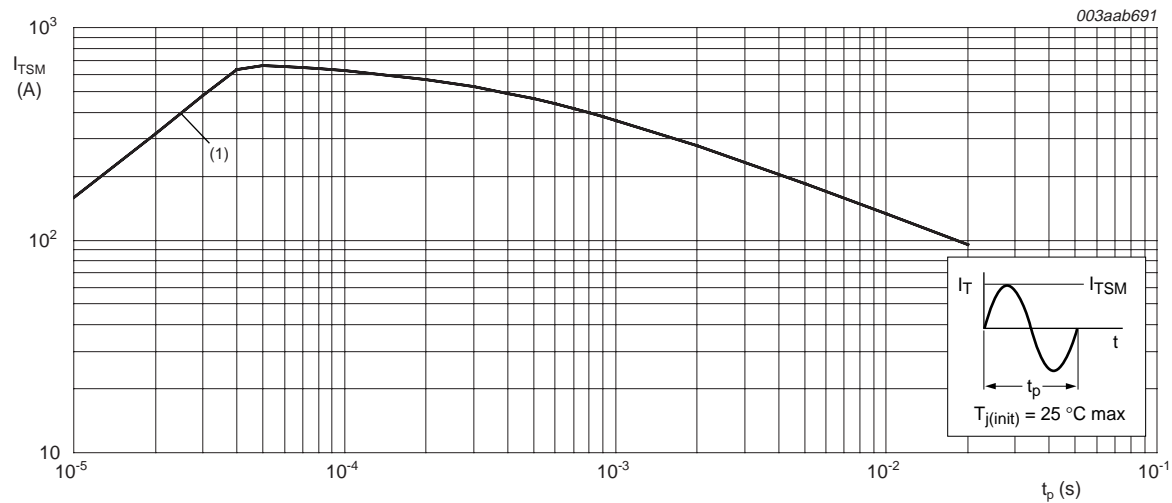
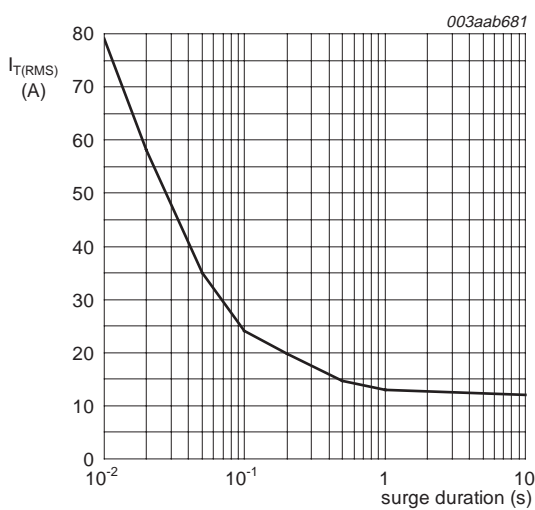


Fig 2. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



$t_p \leq 20$  ms  
(1)  $di_T/dt$  limit

Fig 3. Non-repetitive peak on-state current as a function of pulse duration; maximum values



$f = 50$  Hz  
 $T_h = 61^\circ\text{C}$

Fig 4. RMS on-state current as a function of surge duration; maximum values

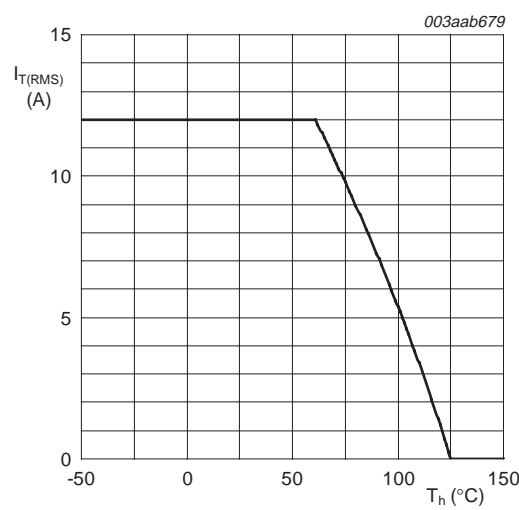
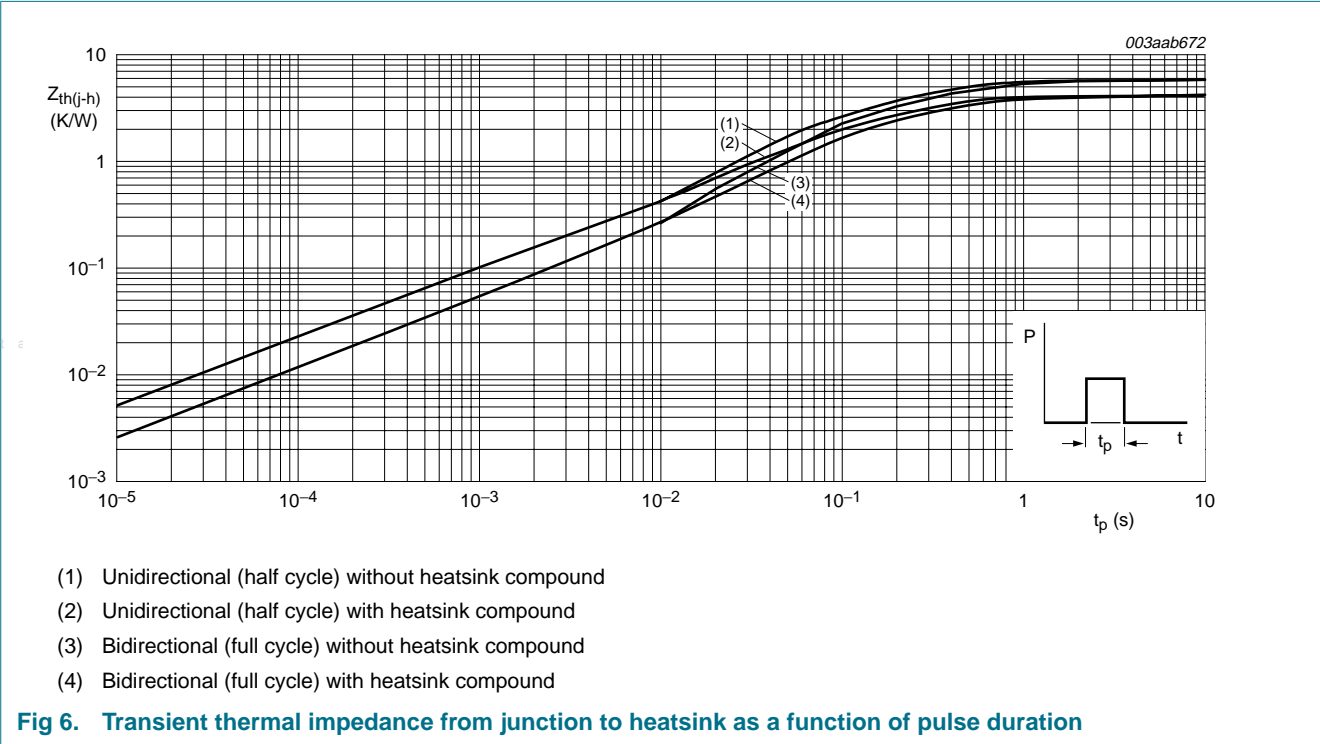


Fig 5. RMS on-state current as a function of heatsink temperature; maximum values

5. Thermal characteristics

Table 4. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to heatsink	full or half cycle; without heatsink compound; see Figure 6	-	-	5.5	K/W
		full or half cycle; with heatsink compound; see Figure 6	-	-	4.0	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	55	-	K/W



6. Isolation characteristics

Table 5. Isolation limiting values and characteristics

$T_h = 25\text{ }^{\circ}\text{C}$  unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{isol(RMS)}$	RMS isolation voltage	from all three terminals to external heatsink; $f = 50\text{ Hz}$ to $60\text{ Hz}$ ; sinusoidal waveform; $RH \leq 65\%$ ; clean and dust free	-	-	2500	V
$C_{isol}$	isolation capacitance	from pin 2 to external heatsink; $f = 1\text{ MHz}$	-	10	-	pF

## 7. Static characteristics

**Table 6. Static characteristics**

$T_j = 25\text{ }^{\circ}\text{C}$  unless otherwise specified.

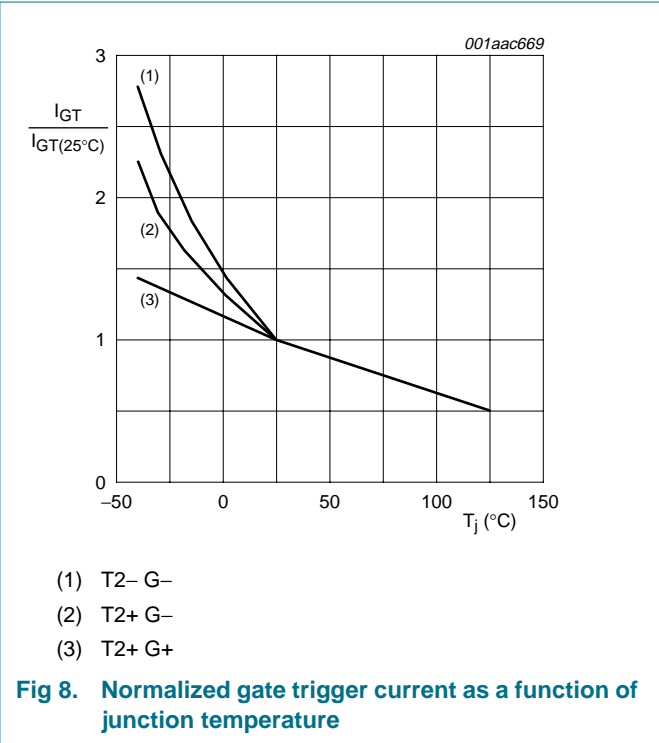
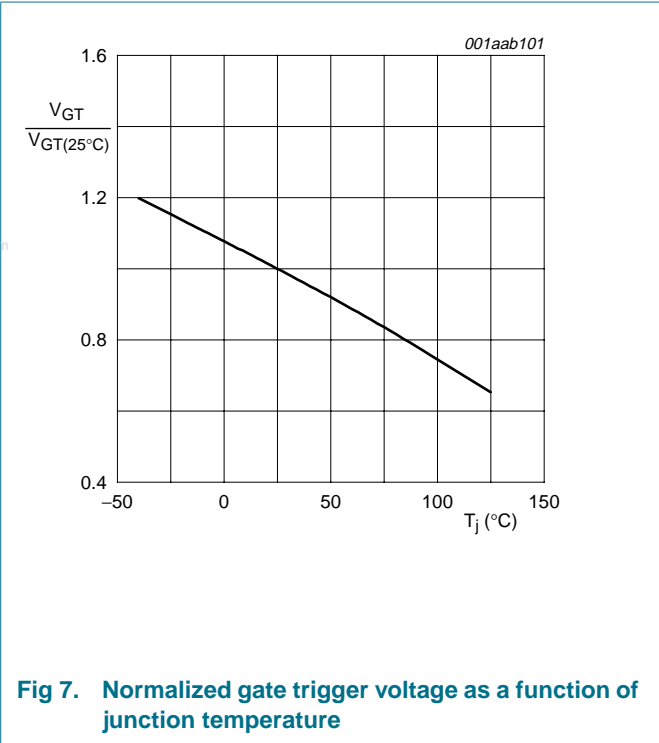
Symbol	Parameter	Conditions	BTA312X-600B BTA312X-800B			BTA312X-600C			Unit
			Min	Typ	Max	Min	Typ	Max	
$I_{GT}$	gate trigger current	$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; see <a href="#">Figure 8</a>							
		T2+ G+	2	-	50	2	-	35	mA
		T2+ G-	2	-	50	2	-	35	mA
		T2- G-	2	-	50	2	-	35	mA
$I_L$	latching current	$V_D = 12\text{ V}$ ; $I_{GT} = 0.1\text{ A}$ ; see <a href="#">Figure 10</a>							
		T2+ G+	-	-	60	-	-	50	mA
		T2+ G-	-	-	90	-	-	60	mA
		T2- G-	-	-	60	-	-	50	mA
$I_H$	holding current	$V_D = 12\text{ V}$ ; $I_{GT} = 0.1\text{ A}$ ; see <a href="#">Figure 11</a>	-	-	60	-	-	35	mA
$V_T$	on-state voltage	$I_T = 15\text{ A}$ ; see <a href="#">Figure 9</a>	-	1.3	1.6	-	1.3	1.6	V
$V_{GT}$	gate trigger voltage	$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; see <a href="#">Figure 7</a>	-	0.8	1.5	-	0.8	1.5	V
		$V_D = 400\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_j = 125\text{ }^{\circ}\text{C}$	0.25	0.4	-	0.25	0.4	-	V
$I_D$	off-state current	$V_D = V_{DRM(max)}$ ; $T_j = 125\text{ }^{\circ}\text{C}$	-	0.1	0.5	-	0.1	0.5	mA

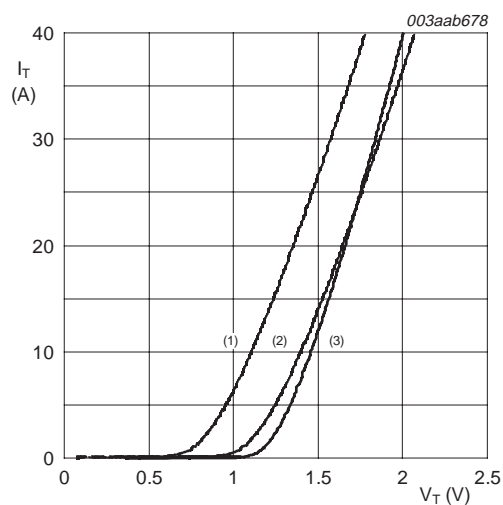
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8. Dynamic characteristics

Table 7. Dynamic characteristics

Symbol	Parameter	Conditions	BTA312X-600B BTA312X-800B			BTA312X-600C			Unit
			Min	Typ	Max	Min	Typ	Max	
$dV_D/dt$	rate of rise of off-state voltage	$V_{DM} = 0.67 \times V_{DRM(max)}$ ; $T_j = 125\text{ }^{\circ}\text{C}$ ; exponential waveform; gate open circuit	1000	2000	-	500	-	-	V/ $\mu\text{s}$
$dI_{com}/dt$	rate of change of commutating current	$V_{DM} = 400\text{ V}$ ; $T_j = 125\text{ }^{\circ}\text{C}$ ; $I_{T(RMS)} = 12\text{ A}$ ; without snubber; gate open circuit	30	-	-	20	-	-	A/ms
$t_{gt}$	gate-controlled turn-on time	$I_{TM} = 20\text{ A}$ ; $V_D = V_{DRM(max)}$ ; $I_G = 0.1\text{ A}$ ; $dI_G/dt = 5\text{ A}/\mu\text{s}$	-	2	-	-	2	-	$\mu\text{s}$





$V_o = 1.127$  V

$R_s = 0.027$   $\Omega$

- (1)  $T_j = 125$  °C; typical values
- (2)  $T_j = 125$  °C; maximum values
- (3)  $T_j = 25$  °C; maximum values

Fig 9. On-state current as a function of on-state voltage

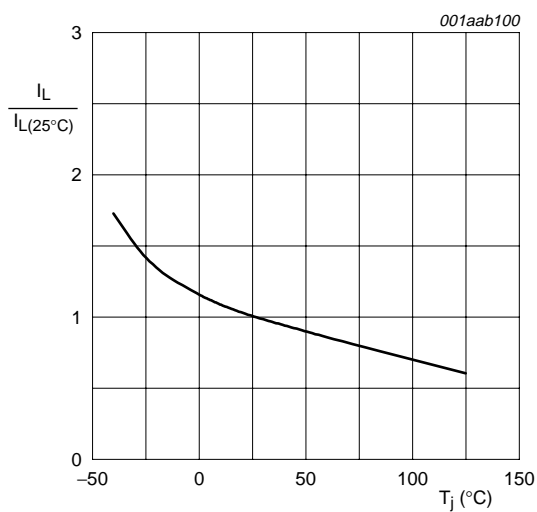


Fig 10. Normalized latching current as a function of junction temperature

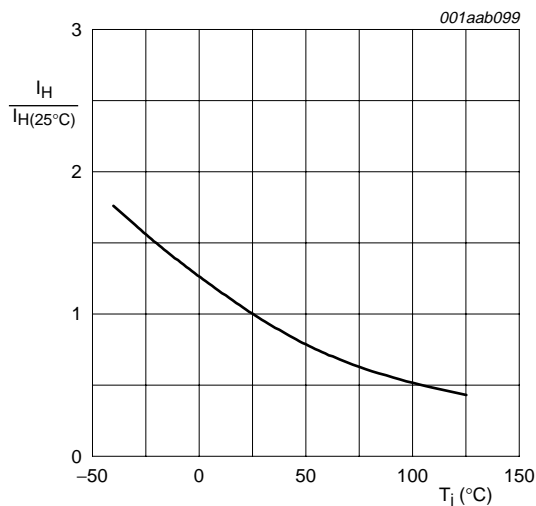


Fig 11. Normalized holding current as a function of junction temperature

## 9. Package information

Epoxy meets UL94 V-0 at 3.175 mm.



10. Package outline

Plastic single-ended package; isolated heatsink mounted;  
1 mounting hole; 3-lead TO-220 'full pack'

SOT186A

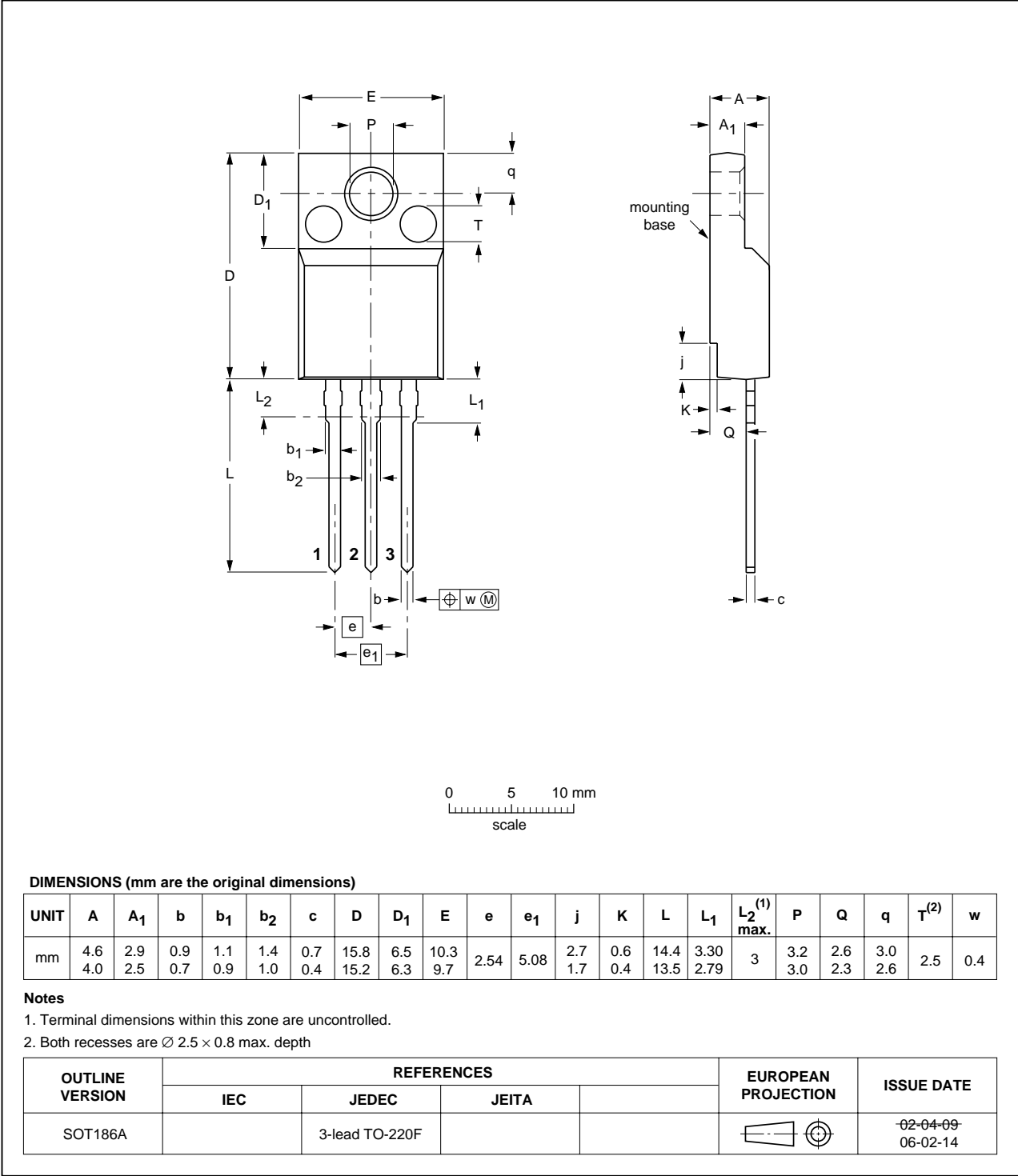


Fig 12. Package outline SOT186A (3-lead TO-220F)

11. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BTA312X_SER_B_C_1	20070411	Product data sheet	-	-

## 12. Legal information

### 12.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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